Demystifying Reliability of Hard Disk and Solid-State Drives

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### Foreword

### This presentation <u>IS</u>:

- A comparative overview of reliability for hard disk drives (HDDs) and solid state disk drives (SSDs)
- Includes reliability specifications; major failure modes & mechanisms; and failure prevention, mitigation and remedies for HDDs, SLC-NAND memory and SSDs (made from the memory)
- A challenge to the HDD community

### This presentation <u>IS NOT</u>:

- A comparison of costs or performance parameters
- A comprehensive discussion of *all* aspects of reliability
- An endorsement of any particular technology
- All one needs to know to recommend HDDs or SSDs



## Agenda

- Reliability claims
  - Smoke and mirrors
  - Claims and statistics

### HDD vs. SSD

- Operation
- Failure modes and effects (some causes)
- Reliability tests in development and manufacturing process
- Problem prevention & remedies
- Open questions and the future
- Conclusions and closing thought



## **SSD Smoke and Mirrors**

#### Source:

B. Crothers, "Samsung defends flash drive reliability" [1]

#### Quotes Michael Yang, Flash Marketing Manager, Samsung

" [wear leveling] makes it virtually impossible to wear out a flash chip. Yang said a pattern could be perpetually repeated in which a 64GB SSD is completely filled with data, erased, filled again, then erased again every hour of every day for years and the user still wouldn't reach the theoretical write limit. He added that if a failure ever does occur, it will not occur in the flash chip itself but in the controller."



## **Reliability Claims**

### Statistically Imprecise Reliability Specifications

### Hard Disks Drives<sup>1</sup>

- $MTBF^6 = 1.4 \text{ M hours } [2]$
- ▶ UCE = 1x10<sup>-16</sup> bits read [3]
- 5 Year Warranty [2]
- None state useful life! Only warranty period.

<sup>1</sup>FCAL Enterprise HDDs <sup>6</sup> Product Specification

### **Solid State Drives<sup>2</sup>**

- MTBF
  - $2 M hours^{3} [4]$
  - 1.7 M hours<sup>3</sup> (64GB) [5]
  - 5 M hours<sup>4</sup> [6]
- ► UCE
  - $-1x10^{-15}$  bits read [5]
  - $-1x10^{-20}$  bits read [7]
- Warranty = 5 years [7]
- Program/Erase (P/E) Endurance Life of 5 year<sup>5</sup> [5]
- <sup>2</sup> 1-bit SLC, NAND Flash
- <sup>3</sup> Handbook prediction
- <sup>4</sup> Extrapolation of test data and assumed usage profile
- <sup>5</sup> 800GB per day,32GB drive; normal operating conditions. Static and dynamic wear-leveling.

## **Reliability Basics - MTBF & Bathtubs** MTBF Basics

Let  $\lambda(t)$  = failure rate

- Only if λ(t) = λ, then MTBF = 1/λ; so failure rate does not change over the product life, from time = 0 and going for ever!! There is no end at which the failure rate increases or decreases
- If the MTBF = 1.4 M hr (constant failure rate), >88% will survive over 20 years and 36.8% will survive >160 years
- The probability of failure in 1 week's time is the same for the first week as for week 10,000
- Stating the MTBF alone is vague. At some point, failure mechanisms change; I don't believe HDDs will survive for 160 years.



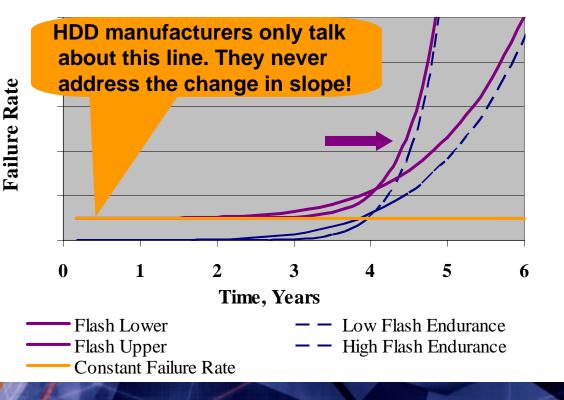
## **Reliability Basics - Bathtub Curve**

### **Bathtub Curves**

Flash/SDD specifications are *slightly better* than HDD at describing assumptions for reliability statements.

Few HDD specifications discuss how usage affects reliability [8] and none have a relationship between usage and end of useful life. However, Flash does! Endurance limit for NAND flash depends on usage, so this chart is WRONG!!

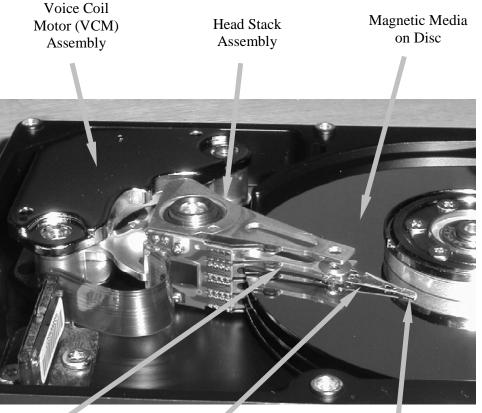
But where are the HDD specs.??? Where do I place the HDD "wear-out" curve?



# HDD Construction & Operation

### Discs spin and heads fly (Duh!)...closely!

- Actuator arm positions head
- Firmware keeps track of physical block location versus logic block
- Separate heads (on each slider) for read and write
- Write current changes direction to change induced magnetic field on disc
- Magnetic orientation on media is preserved as long as no "significant" magnetic fields come near



Suspension

Slider, including Read/Write Element (GMR Head)



Actuator Arm

## **HDD Failure Modes**

### HDD Symptoms, Can't:

- get on track
- stay on track (NRRO, etc.)
- read data quickly enough (time-out)
- write data
- read data

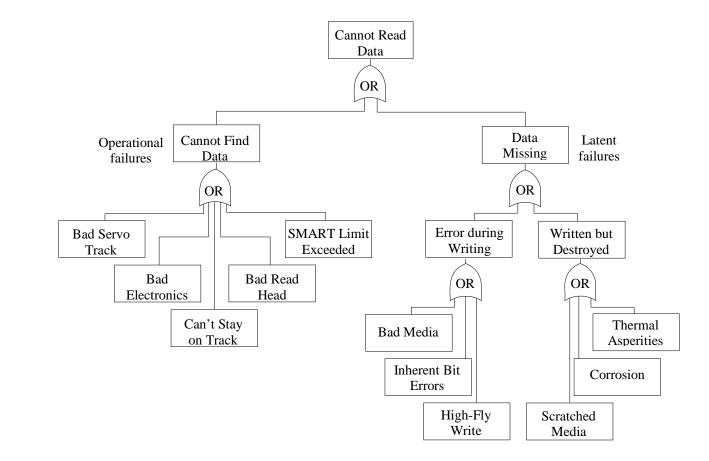
### **Components involved:**

- head related
  - unstable
  - failed
  - flying too high
- media
  - defects
  - scratches
- motors
- electronics (DRAM)
- firmware and servo



### **HDD Failure Modes & Effects**

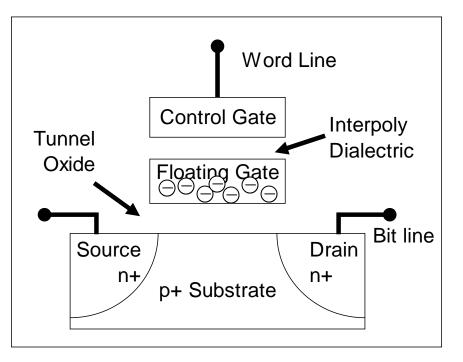
### Symptoms, modes, mechanisms and causes





## **NAND-SLC Flash Construction & Operation**

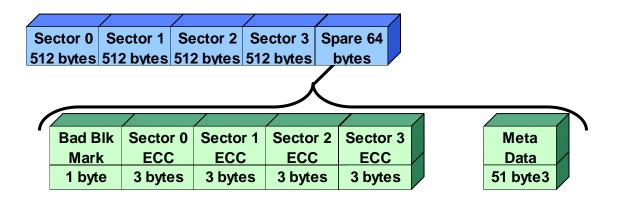
High energy is used to transport charge through the oxide by Fowler-Nordheim (FN) tunneling for erasure or channel hot electron (CHE) injection for programming [9]



At the Floating Gate: + is Logic 1 (erased) - is Logic 0 (programmed)



# **NAND-SLC Flash Construction & Operation** Page Layout for 2048<sup>7</sup> NAND SLC Flash [10]



1 sector = 512 bytes

- 1 page = 4 sectors + ECC/spares = 2048 + 64 bytes
- 1 block = 64 pages = 128k + 4k bytes
- 1 device = 2048 blocks = 2,112MB

Blocks are the smallest erasable units (128k + 4k bytes) Pages are the smallest programmable units (2048 bytes)

<sup>7</sup>Most manufacturers are moving towards 4096 bytes

## Flash/SSD Failure Modes & Effects

- Permanent failure: bit is stuck and cannot change
- <u>Endurance</u>: Stuck cells due to charge-trapping in oxide layer or breakdown of the oxide. Not recoverable by an erase; mark cells as bad and do not use [11]<sup>8</sup>
- Program disturb: Cells not being programmed receive elevated voltage stress. Always in block being programmed. Can be on unselected page or selected page that is not supposed to be programmed. Erase returns cells to undisturbed levels
- <u>Read disturb</u>: In the block being read, but always on pages NOT being read. Erase returns the cells to undisturbed levels
- Data Retention: Floating gate charge is reduced due to charge leakage through oxide defects. Block can be reprogrammed, but retention may not be as long as "pristine" oxide layer

<sup>8</sup>[12] states trapped charge effects can be reversed with an erase

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## Flash/SSD Reliability Relationships

### Time/Use dependent relationships

A

Endurance: Specification is 100,000 P/E cycles (perfect wear-leveling)

 $\frac{100,000 \ P/E \ cycles}{device} x \frac{60,000 \ MB}{P/E \ cycle} x \frac{\sec.}{50 \ MB} x \frac{hour}{3600 \ sec.} x \frac{year}{8760 \ hours} = 3.8 \frac{years}{device}$ 

 <u>Data Retention</u>: Retention as function of time and temperature through Arrhenius relationship [12].

$$F = e^{-\frac{E_a}{k} \left(\frac{1}{T_1} - \frac{1}{T_2}\right)}$$
 Where  

$$AF = Acceleration factor$$

$$E_a = 0.6 \text{ eV} = Activation \text{ energy}$$

$$k = \text{Speed Constant} = 86.25 \times 10^{-6}$$

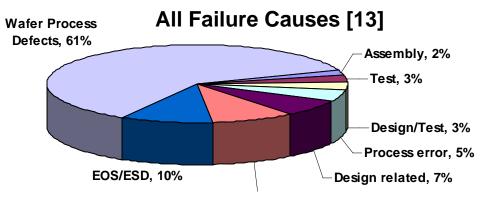
$$T1 = \text{Temperature 1 (K)}$$

$$T2 = \text{Temperature 2 (K)}$$

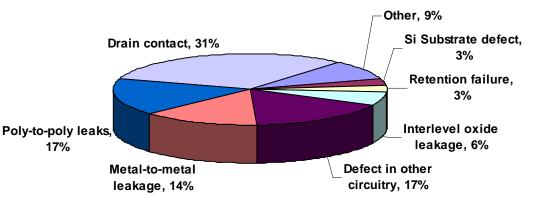


## **Flash Memory Failures**

- Field Data Compilation [13]
  - 2006, NOR Flash is "largely applicable to NAND flash"
  - Non-confirmed failures (at the FA lab) and repetitive cases are omitted
  - Wafer process defects are <u>dominated</u> by particle contamination. Are these the 0.4% that are accounted for in the MTBF specifications?
- Perspective: "Quality levels for SSDs for PCs are very difficult to achieve in many aspects. Only companies that have direct fab control can succeed to get the appropriate quality levels." [4]



#### Wafer Process Defect related [13]





## HDD & SSD Tests

### **HDDs-Mature Industry**

- Much consistency across suppliers
- Development Tests
  - DVT
  - ESS/EOS
  - Shock/vib.
  - Multiple RDTs (reliability demonstration tests)
- Test Conditions
  - Unproven acceleration factors
  - Vague relationship between usage failure rates
- Manufacturing Processes
  - Vintage to vintage life-time variability [last year's presentation]
- Complex f/w; years of experience

### **SSD-Immature Industry**

- Little consistency across suppliers
- Development Tests
  - DVT
  - ESS/EOS
  - Shock/vib.
  - RDT (inconsistent from mfgr to mfgr.)
- Test Conditions
  - Inconsistent
  - No common set of conditions (sample size, environments)
  - Known acceleration factors
  - Known dependence on use
- Manufacturing Processes
  - Lot-to-lot variability REAL issue!
- Low extent of f/w maturity



## HDD & SSD Problem/Mitigation Comparison

### HDDs

- SMART (not very effective)
- ECC on fly (critical to reliability)
- Reallocation of bad sectors. Spare blocks distributed around the surfaces of the discs for reallocation
- Scrub and correct latent defects
- 4k sectors (greater ECC capability)
- Mechanisms that require replacing entire HDD are common (heads and particles)
- "the SSD still falls short when compared with HDDs, which have virtually unlimited write cycles per bit." [14]
- Minimum number of bytes to map out is a sector (512 bytes or, soon, 4k bytes)

### SSD

- SMART (Not the same as for HDDs; limited use; no standard)
- ECC correct read and write disturbed bits (critical to reliability)
- Reallocate bad blocks (2-3%)
- Wear leveling (static & dynamic)
- Dynamic bad block detection and tracking before and after data is written. Map out questionable blocks. Not user selectable. Built into product
- Mechanisms causing entire SSD to fail are uncommon (very low probability)
- Minimum number of bytes to map out is a block (256 sectors, 128k bytes for 2k byte pages or 256k bytes for 4k byte pages)
- Reliability vs. time relationships better understood than for HDDs



## **SSD Open Questions**

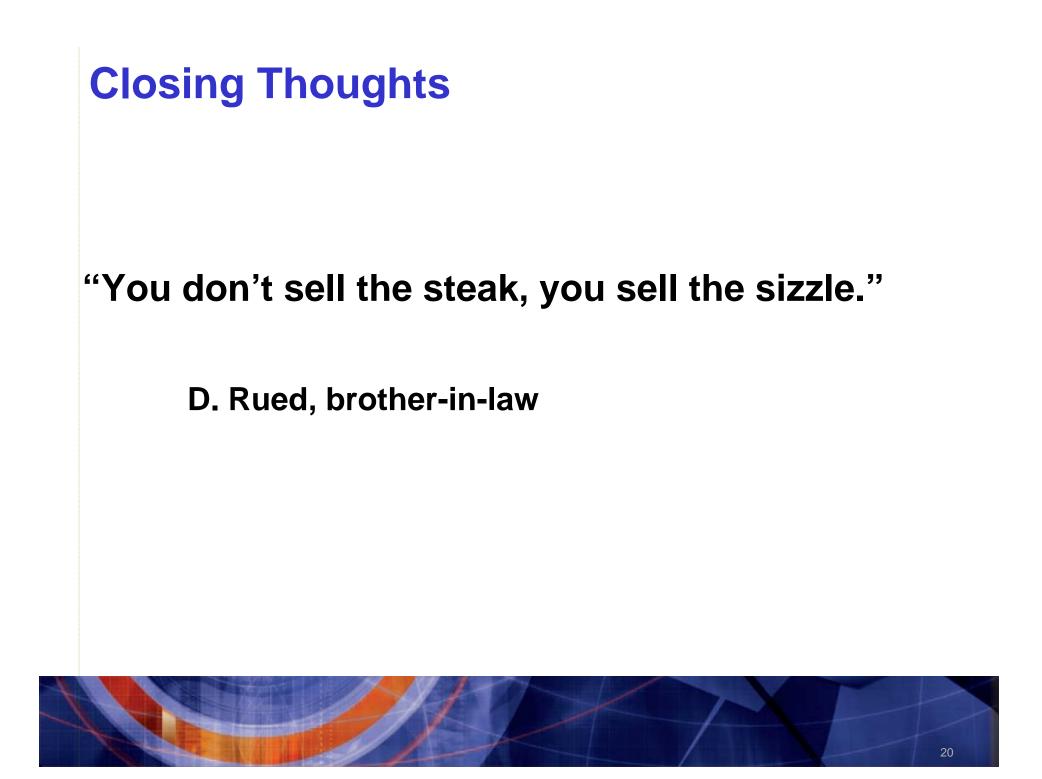
- Statistical Data
  - Distribution of cycles to failure
  - Field failure data
  - Server (NetApp) usage profile
- Qualification tests
  - How are they conducted
  - Definition of failure
  - Quantity tested
- Production Control, as it affects reliability
  - Lot-to-lot variability quantified/controlled?
  - ORT conducted?
  - Burn-in? Why (or why not?)
- Failure Consequences
  - Data retrieval from the remainder of the device after cell/sector/page/block failure?
  - What "whole device" failure modes/mechanisms/causes are there?
  - (controller itself..material limitation in the NAND devices



## Conclusions

- SSD adoption depends on many performance issues for specific applications, not just reliability
- SSD reliability highly dependent on application. SSDs not more reliable than HDDs in all applications & less reliable in some
- SSD returns for performance problems (as is the case today in the PC industry) are perceived as reliability issues
- Flash has the entire semiconductor industry helping resolve some issues (density, contamination)
- Statistical relationships for reliability and time are better quantified for flash than HDDs (acceleration factors and endurance)
- SSD f/w in infancy; inconsistent across competitors
- SSDs not as reliable as all the "hype" in all cases, but potentially a strong competitor in many applications





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